

## ELECTROCALLY CONDUCTIVE EPOXY RESINS, TWO-COMPONENT\*

REF	MIX RATIO	CURING SCHEDULE Recommended	POT LIFE After mixing	VISCOSITY	Tg	DEGRADATION	FILLER	THERMAL EXPANSION		RESISTIVITY	COMMENTS
								BEFORE TG	AFTER TG		
E201	2/3	5 min at 150°C	8 h at 25°C	3 Pa.s	70-80°C	380-400°C	71,5%	40-50.10 <sup>-6</sup> /°C	90-100.10 <sup>-6</sup> /°C	<1 mΩ.cm	Sticking chips onto a lead frame in the manufacture of semiconductors
E202	1/1	5 min at 150°C	8 h at 25°C	1 Pa.s	70-80°C	380-400°C	72%	40-50.10 <sup>-6</sup> /°C	90-100.10 <sup>-6</sup> /°C	<1 mΩ.cm	Sticking chips onto a lead frame in the manufacture of semiconductors - Low volatile rate - Designed for small drop deposites
E203	1/1	25 min at 150°C	8 h at 25°C	2 Pa.s	40-50°C	330-400°C	79%	50-60.10 <sup>-6</sup> /°C	100-120.10 <sup>-6</sup> /°C	<1 mΩ.cm	Semi-flexible conductor bonding on polyester
E204	1/1	5 min at 150°C	8 h at 25°C	0,75 Pa.s	70-80°C	380-400°C	74,5%	50-60.10 <sup>-6</sup> /°C	170-1800.10 <sup>-6</sup> /°C	<1 mΩ.cm	Die-bonding of silicium - Liquid resin
E205	1/1	3 min at 150°C	8 h at 25°C	2 Pa.s	70-80°C	390-400°C	71,5%	50-60.10 <sup>-6</sup> /°C	100-120.10 <sup>-6</sup> /°C	<1 mΩ.cm	Bonding polyester circuits - Curing at low temperature
E206	10/0,8	10 min at 100°C	1 h at 25°C	8 Pa.s	40-50°C	> 350°C	55%	40-50.10 <sup>-6</sup> /°C	90-100.10 <sup>-6</sup> /°C	<10 mΩ.cm	Wire bonding
E207	10/0,2	48 h at 25°C	6 h at 25°C	3,5 Pa.s	80-100°C	> 350°C	76,5%	40-50.10 <sup>-6</sup> /°C	90-100.10 <sup>-6</sup> /°C	0,3 mΩ.cm	Good electric conductivity after curing at low temperature - Conform ESA PSS-01-702
E212	1/1	5 min at 150°C	2 days at 25°C	1,5 Pa.s	80-90°C	350-370°C	71%	50-60.10 <sup>-6</sup> /°C	150-180.10 <sup>-6</sup> /°C	<1 mΩ.cm	Die-bonding of silicium - Silk screening
E212LF	1/1	5 min at 150°C	2 days at 25°C	25 Pa.s	70-80°C	380-410°C	70%	55-65.10 <sup>-6</sup> /°C	100-110.10 <sup>-6</sup> /°C	<0,3 mΩ.cm	Perfectly adapted for the lead free solder resist
E212M	1/1	5 min at 150°C	2 days at 25°C	0,8 Pa.s	70-80°C			50-60.10 <sup>-6</sup> /°C		<0,5 mΩ.cm	Die-bonding of silicium - Silk screening - More liquid of E212
E212M-1	100/2	5 min at 150°C	1 day at 25°C	3 Pa.s	70-90°C	390-410°C		40-50.10 <sup>-6</sup> /°C	110-120.10 <sup>-6</sup> /°C	<0,3 mΩ.cm	Silk screening conductive track or die bonding - Good definition with silk screening
E215	2/1	5 min at 100°C	4 h at 25°C	10 Pa.s	70-90°C	390-410°C	73%	40-50.10 <sup>-6</sup> /°C	110-120.10 <sup>-6</sup> /°C	<0,3 mΩ.cm	Sticking the chips onto the card's flexible circuit - Very fast cure
E300	1/1	1 h at 200°C	8 h at 25°C	500 Pa.s	60-80°C	350-360°C		80-90.10 <sup>-6</sup> /°C	430-450.10 <sup>-6</sup> /°C	10 à 15 Ω.cm	Low cost - Graphite filler
E301	1/1	24 h at 20°C	1 day at 25°C	500 Pa.s	70-90°C	350-360°C		80-90.10 <sup>-6</sup> /°C	430-450.10 <sup>-6</sup> /°C	2500 Ω.cm	Low temperature curing - Graphite filler

The information in this sheet is based on data measurements which we believe to be correct. Epotecny, however, does not accept responsibility for the adaptation of this product to any particular use.

\* for more precision on the technical properties, to refer to the individual data sheet.

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